



**Amendment to the Specification.**

Please amend paragraph [0029] as follows:

A1 [0029] The contact region 50 may comprise an alloy of the contact layer 34 and wide band-gap semiconductor material 32 and form a substantially ohmic connection to be made between the material 32 and the contact layer 34 as shown in FIG. 5. Compare to FIG. 1 in which a contact layer 12 has suffered from balling, melting, and peeling as may happen when annealed at temperatures above the melting point of the contact layer 12. Unlike FIG. 1, the contact region 30 of the embodiment as illustrated in FIG. 5 may be substantially continuous and free of significant discontinuities 40 due to peeling, balling, melting, or other mechanisms that could affect the contact layer 34 during annealing. Additionally, the contact region 32 may not extend entirely through the wide band-gap semiconductor 10 to underlying layer 42, causing an electrical short.

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